

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE (PCT PROCESS)

2SC3138

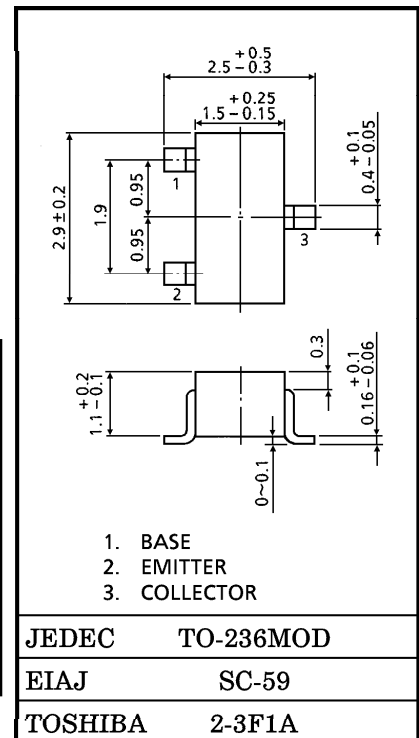
HIGH VOLTAGE SWITCHING APPLICATIONS

- High Voltage : $V_{CBO}=200V$ (Min.)
 $V_{CEO}=200V$ (Min.)
- Small Flat Package
- Complementary to 2SA1255

MAXIMUM RATINGS ($T_a = 25^\circ C$)

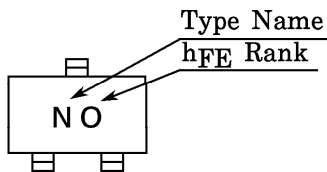
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	200	V
Collector-Emitter Voltage	V_{CEO}	200	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	50	mA
Base Current	I_B	20	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	125	$^\circ C$
Storage Temperature Range	T_{stg}	-55~125	$^\circ C$

Unit in mm



Weight : 0.012g

MARKING



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 200V, I_E = 0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	—	—	0.1	μA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 0.1mA, I_E = 0$	200	—	—	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	200	—	—	V
DC Current Gain	h_{FE} (Note)	$V_{CE} = 3V, I_C = 10mA$	70	—	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$	—	0.1	0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 10mA, I_B = 1mA$	—	0.75	1.5	V
Transition Frequency	f_T	$V_{CE} = 10V, I_C = 2mA$	50	100	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	2	4	pF
Switching Time	Turn on Time	$V_{CC} = 50V, I_C = 6mA,$ $I_{B1} = -I_{B2} = 0.6mA,$ Pulse Width = $5\mu s,$ Duty Cycle $\leq 2\%$	—	0.3	—	μs
	Storage Time		—	2	—	
	Fall Time		—	0.4	—	

(Note) : h_{FE} Classification O : 70~140, Y : 120~240

